# Abstracts

## A 20GHz Silicon Microwave Monolithic Integrated Circuits Process and a 7.4GHz Frequency Divider

*S. Miyazaki, C. Takai, K. Eguchi and T. Nakata. "A 20GHz Silicon Microwave Monolithic Integrated Circuits Process and a 7.4GHz Frequency Divider." 1989 MTT-S International Microwave Symposium Digest 89.3 (1989 Vol. III [MWSYM]): 1065-1068.*

A Silicon Microwave Monolithic Integrated Circuits process named "DNP-III" has been developed without self-alignment technique. By using "DNP-III" process. NPN transistors with 0.6µm width and 0.1µm depth emitter achieved f/sub T/ of 20 GHz. Maximum dividing frequency (Fmax) of 7.4GHz at Vcc=6V was also achieved for 1/2 prescaler with master slave T-type flip-flop.

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